

IN THE SPECIFICATION

Page 1, prior to "FIELD OF THE INVENTION" insert the paragraph:

a'
--This application is a division of U.S. Serial No. 09/064,165, filed April 22, 1998,
now pending.--

✓ Page 2, line ¹⁹20, change "titan-tungsten" to --titanium-tungsten--.

✓ Page 3, line ²²23, change "titan-tungsten" to --titanium-tungsten--.

✓ Page 5, line 4, change "titan-tungsten" to --titanium-tungsten--.

✓ Page 6, line 20, change "titan-tungsten" to --titanium-tungsten--.

✓ Page 7, line 15, change "titan-" to --titanium--

✓ Page 8, lines 10-12, delete in their entirety and insert electrode pad 70; and

a'
(2) the third interlayer insulating film 60c made of PSG or BPSG, and the barrier metal
layer 63 made of a refractory metal such as titanium-tungsten do--.

✓ Page 8, line 12, change "titan-tungsten" to --titanium-tungsten--.

✓ Page 14, line 13, change "12(b)" to --12(d)--.

✓ Page 16, line 21, change "titan-tungsten" to --titanium-tungsten--.

✓ Page 18, line 10, change "titan-tungsten" to --titanium-tungsten--;

✓ Page 18, line 20, change "titanic" to --tungsten--.

✓ Page 19, line 22, change "titan" to --titanium--.

✓ Page 20, line 14, change "titan" to --titanium--.

✓ Page 21, line 17, change "titan" to --titanium--.

✓ Page 22, line 24, change "titan" to --titanium--.

- ✓ Page 23, line 13, change "titan" to --titanium--.
- ✓ Page 26, line 21, change "titanic" to --titanium--; and
- ✓ Page 26, line 23, change "titan" to --titanium--.

IN THE CLAIMS

- ✓ Cancel claims 1 through 13, 17 through 21, 23 and 24.
- ✓ Amend claims 14 through 16, 22 and 25 as follows:
- ✓ Claim 14, line 5, change "formed so as to cover" to --covering--;
- ✓ Claim 14, line 8, delete "being provided".
- ✓ Claim 15, line 5, change "formed so as to cover" to --covering--.
- ✓ Claim 16, line 3, change "being formed so as to cover" to --covering--.

Subt B²
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22. (Amended) A semiconductor device, comprising:

- an active element provided on a semiconductor substrate;
- a lower interlayer insulating film formed so as to cover said active element;
- a metal wire provided on said lower interlayer insulating film;
- an upper interlayer insulating film formed so as to cover said metal wire; and
- a pad metal for an electrode pad, said pad metal being provided on said upper interlayer insulating film,

wherein each of said lower and upper interlayer insulating films have a trilaminar structure, each of first and third layers of the trilaminar film being a silicon nitride film or a silicon oxide film, while a second layer of the trilaminar film being [formed by the] spin-on-glass [method];